

FEATURES

- 0.5 Ω typical on resistance**
- 0.8 Ω maximum on resistance at 125°C**
- 1.65 V to 3.6 V operation**
- Automotive temperature range: -40°C to +125°C**
- High current carrying capability: 300 mA continuous**
- Rail-to-rail switching operation**
- Fast-switching times <20 ns**
- Typical power consumption (<0.1 μ W)**

APPLICATIONS

- Cellular phones
- PDA's
- MP3 players
- Power routing
- Battery-powered systems
- PCMCIA cards
- Modems
- Audio and video signal routing
- Communication systems

GENERAL DESCRIPTION

The ADG836 is a low voltage CMOS device containing two independently selectable single-pole, double-throw (SPDT) switches. This device offers ultralow on resistance of less than 0.8 Ω over the full temperature range. The ADG836 is fully specified for 3.3 V, 2.5 V, and 1.8 V supply operation.

Each switch conducts equally well in both directions when on, and has an input signal range that extends to the supplies. The ADG836 exhibits break-before-make switching action.

The ADG836 is available in a 10-lead MSOP and a 3 mm \times 3 mm 12-lead LFCSP.

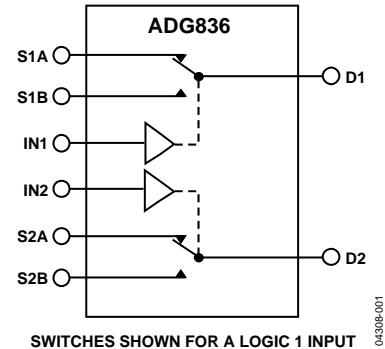


Figure 1.

PRODUCT HIGHLIGHTS

1. <0.8 Ω over full temperature range of -40°C to +125°C.
2. Single 1.65 V to 3.6 V operation.
3. Compatible with 1.8 V CMOS logic.
4. High current handling capability (300 mA continuous current at 3.3 V).
5. Low THD + N (0.02% typ).
6. 3 mm \times 3 mm LFCSP package and 10-lead MSOP package.

Rev. A

Information furnished by Analog Devices is believed to be accurate and reliable. However, no responsibility is assumed by Analog Devices for its use, nor for any infringements of patents or other rights of third parties that may result from its use. Specifications subject to change without notice. No license is granted by implication or otherwise under any patent or patent rights of Analog Devices. Trademarks and registered trademarks are the property of their respective owners.

TABLE OF CONTENTS

| | | | |
|-------------------------------|---|---|----|
| Specifications..... | 3 | Typical Performance Characteristics | 8 |
| Absolute Maximum Ratings..... | 6 | Test Circuits..... | 11 |
| ESD Caution..... | 6 | Outline Dimensions | 13 |
| Pin Configurations | 7 | Ordering Guide | 13 |

REVISION HISTORY

4/05—Rev. 0 to Rev. A

| | |
|---------------------------------|-----------|
| Updated Format..... | Universal |
| Changes to Table 1..... | 3 |
| Changes to Table 2..... | 4 |
| Changes to Table 3..... | 5 |
| Changes to Ordering Guide | 13 |

Revision 0: Initial Version

SPECIFICATIONS

$V_{DD} = 2.7\text{ V to }3.6\text{ V}$, $GND = 0\text{ V}$, unless otherwise noted.

Table 1.

| Parameter | Temperature ¹ | | | Unit | Test Conditions/Comments |
|---|--------------------------|----------------|-----------------|-------------------|---|
| | +25°C | -40°C to +85°C | -40°C to +125°C | | |
| ANALOG SWITCH | | | | | |
| Analog Signal Range | | | 0 V to V_{DD} | V | |
| On Resistance (R_{ON}) | 0.5 | | | Ω typ | $V_{DD} = 2.7\text{ V}$, $V_S = 0\text{ V to }V_{DD}$, $I_S = 100\text{ mA}$; Figure 19 |
| | 0.65 | 0.75 | 0.8 | Ω max | |
| On Resistance Match | 0.04 | | | Ω typ | $V_{DD} = 2.7\text{ V}$, $V_S = 0.65\text{ V}$, $I_S = 100\text{ mA}$ |
| Between Channels (ΔR_{ON}) | | 0.075 | 0.08 | Ω max | |
| On Resistance Flatness ($R_{FLAT(ON)}$) | 0.1 | | | Ω typ | $V_{DD} = 2.7\text{ V}$, $V_S = 0\text{ V to }V_{DD}$ |
| | | 0.15 | 0.16 | Ω max | $I_S = 100\text{ mA}$ |
| LEAKAGE CURRENTS | | | | | |
| Source Off Leakage I_S (OFF) | ± 0.2 | | | nA typ | $V_{DD} = 3.6\text{ V}$ $V_S = 0.6\text{ V}/3.3\text{ V}$, $V_D = 3.3\text{ V}/0.6\text{ V}$; Figure 20 |
| Channel On Leakage I_D , I_S (ON) | ± 0.2 | | | nA typ | $V_S = V_D = 0.6\text{ V or }3.3\text{ V}$; Figure 21 |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, V_{INH} | | | 2 | V min | |
| Input Low Voltage, V_{INL} | | | 0.8 | V max | |
| Input Current | | | | μA typ | $V_{IN} = V_{INL}$ or V_{INH} |
| I_{INL} or I_{INH} | 0.005 | | | μA max | |
| | | | ± 0.1 | μA max | |
| C_{IN} , Digital Input Capacitance | 4 | | | pF typ | |
| DYNAMIC CHARACTERISTICS² | | | | | |
| t_{ON} | 21 | | | ns typ | $R_L = 50\ \Omega$, $C_L = 35\text{ pF}$ |
| | 26 | 28 | 29 | ns max | $V_S = 1.5\text{ V}/0\text{ V}$; Figure 22 |
| t_{OFF} | 4 | | | ns typ | $R_L = 50\ \Omega$, $C_L = 35\text{ pF}$ |
| | 7 | 8 | 9 | ns max | $V_S = 1.5\text{ V}$; Figure 22 |
| Break-Before-Make Time Delay (t_{BBM}) | 17 | | 5 | ns typ | $R_L = 50\ \Omega$, $C_L = 35\text{ pF}$ |
| | | | | ns min | $V_{S1} = V_{S2} = 1.5\text{ V}$; Figure 23 |
| Charge Injection | 40 | | | pC typ | $V_S = 1.5\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; Figure 24 |
| Off Isolation | -67 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; Figure 25 |
| Channel-to-Channel Crosstalk | -90 | | | dB typ | S1A-S2A/S1B-S2B, $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; Figure 28 |
| | -67 | | | dB typ | S1A-S1B/S2A-S2B, $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; Figure 27 |
| Total Harmonic Distortion (THD + N) | 0.02 | | | % | $R_L = 32\ \Omega$, $f = 20\text{ Hz to }20\text{ kHz}$, $V_S = 2\text{ V p-p}$ |
| Insertion Loss | -0.05 | | | dB typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; Figure 26 |
| -3 dB Bandwidth | 57 | | | MHz typ | $R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; Figure 26 |
| C_S (OFF) | 25 | | | pF typ | |
| C_D , C_S (ON) | 75 | | | pF typ | |
| POWER REQUIREMENTS | | | | | |
| I_{DD} | 0.003 | | | μA typ | $V_{DD} = 3.6\text{ V}$ |
| | | 1 | 4 | μA max | Digital inputs = 0 V or 3.6 V |

¹ Temperature range for Y version is -40°C to +125°C.

² Guaranteed by design, not subject to production test.

ADG836

$V_{DD} = 2.5 \text{ V} \pm 0.2 \text{ V}$, $GND = 0 \text{ V}$, unless otherwise noted.

Table 2.

| Parameter | Temperature ¹ | | | Unit | Test Conditions/Comments |
|--|--------------------------|----------------|-----------------|-------------------|---|
| | +25°C | -40°C to +85°C | -40°C to +125°C | | |
| ANALOG SWITCH | | | | | |
| Analog Signal Range | | | 0 V to V_{DD} | V | |
| On Resistance (R_{ON}) | 0.65 | | | Ω typ | $V_{DD} = 2.3 \text{ V}$, $V_S = 0 \text{ V to } V_{DD}$, $I_S = 100 \text{ mA}$; Figure 19 |
| | 0.72 | 0.8 | 0.88 | Ω max | |
| On Resistance Match Between Channels (ΔR_{ON}) | 0.04 | | | Ω typ | $V_{DD} = 2.3 \text{ V}$, $V_S = 0.7 \text{ V}$, $I_S = 100 \text{ mA}$ |
| | | 0.08 | 0.085 | Ω max | |
| On Resistance Flatness ($R_{FLAT(ON)}$) | 0.16 | | | Ω typ | $V_{DD} = 2.3 \text{ V}$, $V_S = 0 \text{ V to } V_{DD}$, $I_S = 100 \text{ mA}$ |
| | | 0.23 | 0.24 | Ω max | |
| LEAKAGE CURRENTS | | | | | |
| Source Off Leakage I_S (OFF) | ± 0.2 | | | nA typ | $V_{DD} = 2.7 \text{ V}$ $V_S = 0.6 \text{ V}/2.4 \text{ V}$, $V_D = 2.4 \text{ V}/0.6 \text{ V}$; Figure 20 |
| Channel On Leakage I_D , I_S (ON) | ± 0.2 | | | nA typ | $V_S = V_D = 0.6 \text{ V or } 2.4 \text{ V}$; Figure 21 |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, V_{INH} | | | 1.7 | V min | $V_{IN} = V_{INL} \text{ or } V_{INH}$ |
| Input Low Voltage, V_{INL} | | | 0.7 | V max | |
| Input Current I_{INL} or I_{INH} | 0.005 | | | μA typ | |
| | | | ± 0.1 | μA max | |
| C_{IN} , Digital Input Capacitance | 4 | | | pF typ | |
| DYNAMIC CHARACTERISTICS² | | | | | |
| t_{ON} | 23 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 \text{ pF}$ |
| | 29 | 30 | 31 | ns max | $V_S = 1.5 \text{ V}/0 \text{ V}$; Figure 22 |
| t_{OFF} | 5 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 \text{ pF}$ |
| | 7 | 8 | 9 | ns max | $V_S = 1.5 \text{ V}$; Figure 22 |
| Break-before-Make Time Delay (t_{BBM}) | 17 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 \text{ pF}$ |
| | | | 5 | ns min | $V_{S1} = V_{S2} = 1.5 \text{ V}$; Figure 23 |
| Charge Injection | 30 | | | pC typ | $V_S = 1.25 \text{ V}$, $R_S = 0 \Omega$, $C_L = 1 \text{ nF}$; Figure 24 |
| Off Isolation | -67 | | | dB typ | $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 100 \text{ kHz}$; Figure 25 |
| Channel-to-Channel Crosstalk | -90 | | | dB typ | S1A-S2A/S1B-S2B, $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 100 \text{ kHz}$; Figure 28 |
| | -67 | | | dB typ | S1A-S1B/S2A-S2B, $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 100 \text{ kHz}$; Figure 27 |
| Total Harmonic Distortion (THD + N) | 0.022 | | | % | $R_L = 32 \Omega$, $f = 20 \text{ Hz to } 20 \text{ kHz}$, $V_S = 1.5 \text{ V p-p}$ |
| Insertion Loss | -0.06 | | | dB typ | $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$; Figure 26 |
| -3 dB Bandwidth | 57 | | | MHz typ | $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$; Figure 26 |
| C_S (OFF) | 25 | | | pF typ | |
| C_D , C_S (ON) | 75 | | | pF typ | |
| POWER REQUIREMENTS | | | | | |
| I_{DD} | 0.003 | | | μA typ | $V_{DD} = 2.7 \text{ V}$ Digital inputs = 0 V or 2.7 V |
| | | 1 | 4 | μA max | |

¹ Temperature range for Y version is -40°C to +125°C.

² Guaranteed by design, not subject to production test.

$V_{DD} = 1.65 \text{ V} \pm 1.95 \text{ V}$, GND = 0 V, unless otherwise noted.

Table 3.

| Parameter | Temperature ¹ | | | Unit | Test Conditions/Comments |
|--|--------------------------|----------------|-----------------|--|---|
| | +25°C | −40°C to +85°C | −40°C to +125°C | | |
| ANALOG SWITCH | | | | | |
| Analogue Signal Range | | | 0 V to V_{DD} | V | |
| On Resistance (R_{ON}) | 1 | | | Ω typ | $V_{DD} = 1.8 \text{ V}$, $V_S = 0 \text{ V}$ to V_{DD} , $I_S = 100 \text{ mA}$; Figure 19 |
| | 1.4 | 2.2 | 2.2 | Ω max | |
| | 2 | 4 | 4 | Ω max | $V_{DD} = 1.65 \text{ V}$, $V_S = 0 \text{ V}$ to V_{DD} , $I_S = 100 \text{ mA}$; Figure 19 |
| On Resistance Match Between Channels (ΔR_{ON}) | 0.1 | | | Ω typ | $V_{DD} = 1.65 \text{ V}$, $V_S = 0.7 \text{ V}$, $I_S = 100 \text{ mA}$ |
| LEAKAGE CURRENTS | | | | | |
| Source Off Leakage I_S (OFF) | ± 0.2 | | | nA typ | $V_{DD} = 1.95 \text{ V}$ $V_S = 0.6 \text{ V}/1.65 \text{ V}$, $V_D = 1.65 \text{ V}/0.6 \text{ V}$; Figure 20 |
| Channel On Leakage I_D , I_S (ON) | ± 0.2 | | | nA typ | $V_S = V_D = 0.6 \text{ V}$ or 1.65 V ; Figure 21 |
| DIGITAL INPUTS | | | | | |
| Input High Voltage, V_{INH} | | | $0.65 V_{DD}$ | V min | |
| Input Low Voltage, V_{INL} | | | $0.35 V_{DD}$ | V max | |
| Input Current I_{INL} or I_{INH} | 0.005 | | | μA typ μA max | $V_{IN} = V_{INL}$ or V_{INH} |
| C_{IN} , Digital Input Capacitance | 4 | | | pF typ | |
| DYNAMIC CHARACTERISTICS² | | | | | |
| t_{ON} | 28 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 \text{ pF}$ |
| | 37 | 38 | 39 | ns max | $V_S = 1.5 \text{ V}/0 \text{ V}$; Figure 22 |
| t_{OFF} | 7 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 \text{ pF}$ |
| | 9 | 10 | 11 | ns max | $V_S = 1.5 \text{ V}$; Figure 22 |
| Break-Before-Make Time Delay (t_{BBM}) | 21 | | | ns typ | $R_L = 50 \Omega$, $C_L = 35 \text{ pF}$ |
| | | | 5 | ns min | $V_{S1} = V_{S2} = 1 \text{ V}$; Figure 23 |
| Charge Injection | 20 | | | pC typ | $V_S = 1 \text{ V}$, $R_S = 0 \text{ V}$, $C_L = 1 \text{ nF}$; Figure 24 |
| Off Isolation | −67 | | | dB typ | $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 100 \text{ kHz}$; Figure 25 |
| Channel-to-Channel Crosstalk | −90 | | | dB typ | S1A–S2A/S1B–S2B; $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 100 \text{ kHz}$; Figure 28 |
| | −67 | | | dB typ | S1A–S1B/S2A–S2B; $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$, $f = 100 \text{ kHz}$; Figure 27 |
| Total Harmonic Distortion, THD | 0.14 | | | % | $R_L = 32 \Omega$, $f = 20 \text{ Hz}$ to 20 kHz , $V_S = 1.2 \text{ V}$ p-p |
| Insertion Loss | −0.08 | | | dB typ | $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$; Figure 26 |
| −3 dB Bandwidth | 57 | | | MHz typ | $R_L = 50 \Omega$, $C_L = 5 \text{ pF}$; Figure 26 |
| C_S (OFF) | 25 | | | pF typ | |
| C_D , C_S (ON) | 75 | | | pF typ | |
| POWER REQUIREMENTS | | | | | |
| I_{DD} | 0.003 | | | μA typ | $V_{DD} = 1.95 \text{ V}$ Digital inputs = 0 V or 1.95 V |
| | | 1.0 | 4 | μA max | |

¹ Temperature range for Y version is −40°C to +125°C.

² Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

T_A = 25°C, unless otherwise noted.

Table 4.

| Parameter | Rating |
|---|--|
| V _{DD} to GND | −0.3 V to +4.6 V |
| Analog Inputs ¹ | −0.3 V to V _{DD} + 0.3 V |
| Digital Inputs ¹ | −0.3 V to 4.6 V or 10 mA, whichever occurs first |
| Peak Current, S or D | |
| 3.3 V Operation | 500 mA |
| 2.5 V Operation | 460 mA |
| 1.8 V Operation | 420 mA (pulsed at 1ms, 10% duty cycle max) |
| Continuous Current, S or D | |
| 3.3 V Operation | 300 mA |
| 2.5 V Operation | 275 mA |
| 1.8 V Operation | 250 mA |
| Operating Temperature Range | |
| Automotive (Y Version) | −40°C to +125°C |
| Storage Temperature Range | −65°C to +150°C |
| Junction Temperature | 150°C |
| MSOP Package | |
| θ _{JA} Thermal Impedance | 206°C/W |
| θ _{JC} Thermal Impedance | 44°C/W |
| LFCSP Package | |
| θ _{JA} Thermal Impedance (3-Layer Board) | 61.1°C/W |
| IR Reflow, Peak Temperature <20 sec | 235°C |

¹ Overvoltages at IN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

Table 5. Truth Table

| Logic | Switch A | Switch B |
|-------|----------|----------|
| 0 | Off | On |
| 1 | On | Off |

PIN CONFIGURATIONS

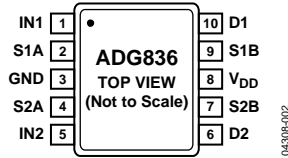


Figure 2. 10-Lead MSOP (RM-10)

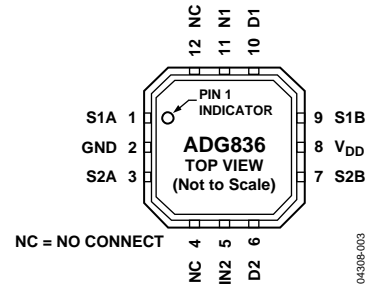


Figure 3. 12-Lead LFCSP (CP-12)

Table 6. Terminology

| | |
|--------------------------------------|--|
| V _{DD} | Most positive power supply potential. |
| I _{DD} | Positive supply current. |
| GND | Ground (0 V) reference. |
| S | Source terminal. May be an input or output. |
| D | Drain terminal. May be an input or output. |
| IN | Logic control input. |
| V _D (V _S) | Analog voltage on terminals D, S. |
| R _{ON} | Ohmic resistance between D and S. |
| R _{FLAT (ON)} | Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range. |
| ΔR _{ON} | On resistance match between any two channels. |
| I _S (OFF) | Source leakage current with the switch off. |
| I _D (OFF) | Drain leakage current with the switch off. |
| I _D , I _S (ON) | Channel leakage current with the switch on. |
| V _{INL} | Maximum input voltage for Logic 0. |
| V _{INH} | Minimum input voltage for Logic 1. |
| I _{INL} (I _{INH}) | Input current of the digital input. |
| C _S (OFF) | Off switch source capacitance. Measured with reference to ground. |
| C _D (OFF) | Off switch drain capacitance. Measured with reference to ground. |
| C _D , C _S (ON) | On switch capacitance. Measured with reference to ground. |
| C _{IN} | Digital input capacitance. |
| t _{ON} | Delay time between the 50% and the 90% points of the digital input and switch on condition. |
| t _{OFF} | Delay time between the 50% and the 90% points of the digital input and switch off condition. |
| t _{BBM} | On or off time measured between the 80% points of both switches when switching from one to another. |
| Charge Injection | A measure of the glitch impulse transferred from the digital input to the analog output during on-off switching. |
| Off Isolation | A measure of unwanted signal coupling through an off switch. |
| Crosstalk | A measure of unwanted signal, which is coupled through from one channel to another, as a result of parasitic capacitance. |
| –3 dB Bandwidth | The frequency at which the output is attenuated by 3 dB. |
| On Response | The frequency response of the on switch. |
| Insertion Loss | The loss due to the on resistance of the switch. |
| THD + N | The ratio of the harmonics amplitude plus noise of a signal to the fundamental. |

TYPICAL PERFORMANCE CHARACTERISTICS

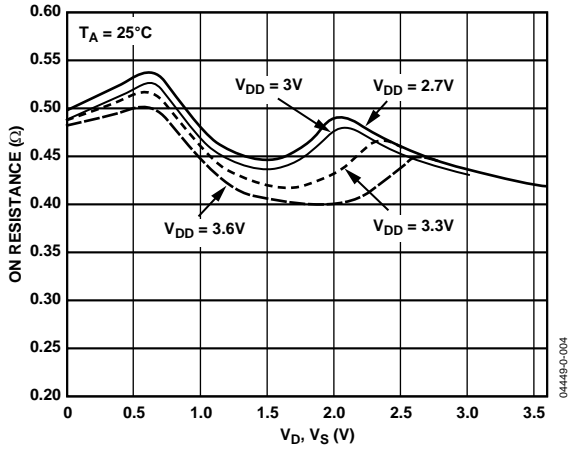


Figure 4. On Resistance vs. V_D (V_S) $V_{DD} = 2.7$ to 3.6 V

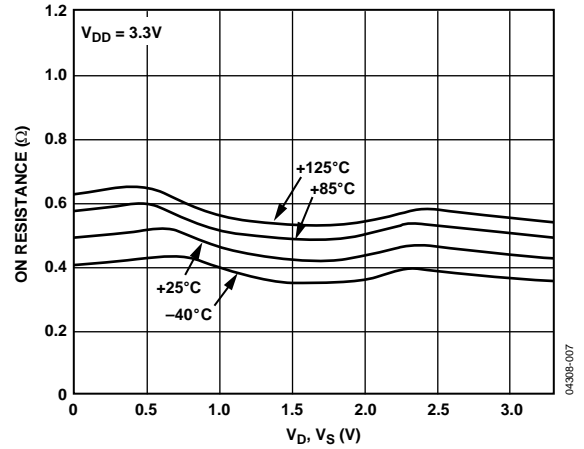


Figure 7. On Resistance vs. V_D (V_S) for Different Temperature, 3.3 V

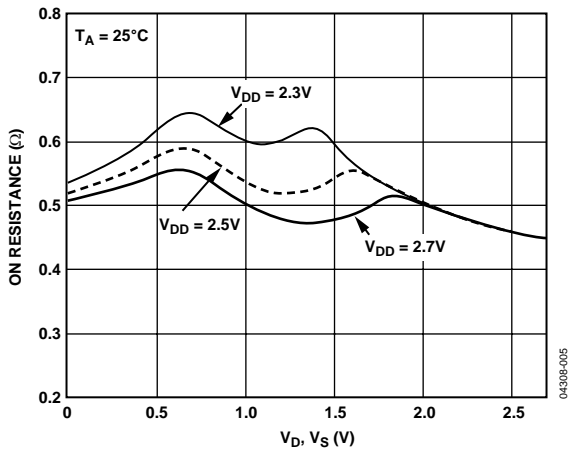


Figure 5. On Resistance vs. V_D (V_S) $V_{DD} = 2.5$ V to 0.2 V

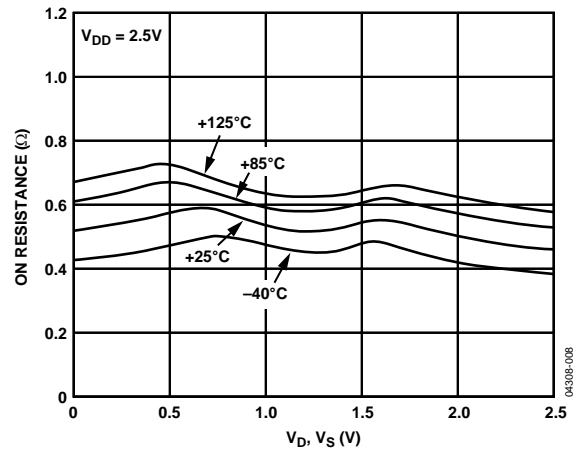


Figure 8. On Resistance vs. V_D (V_S) for Different Temperature, 2.5 V

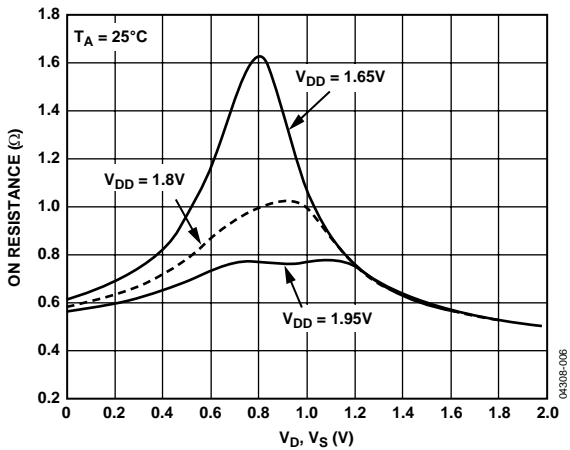


Figure 6. On Resistance vs. V_D (V_S) $V_{DD} = 1.8 \pm 3.6$

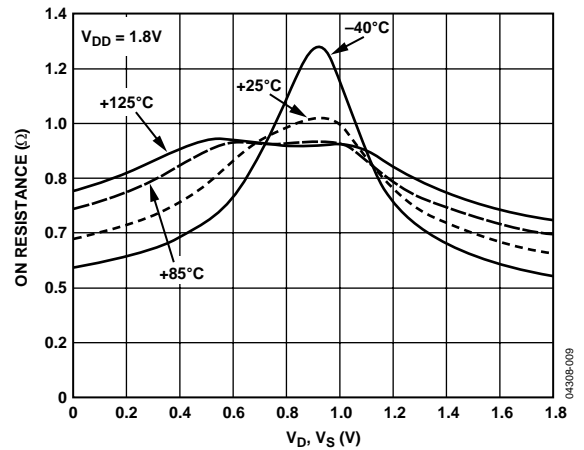


Figure 9. On Resistance vs. V_D (V_S) for Different Temperature, 1.8 V

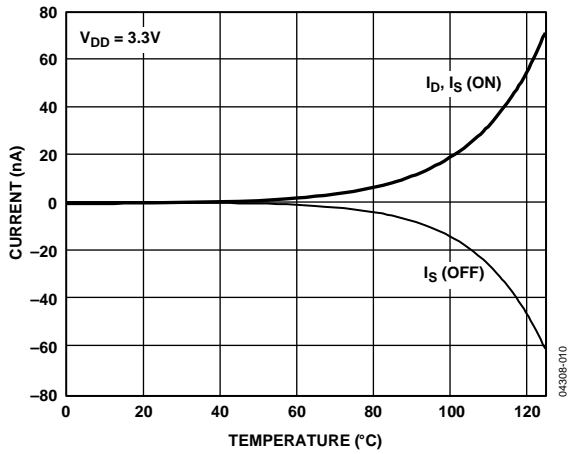


Figure 10. Leakage Current vs. Temperature, 3.3 V

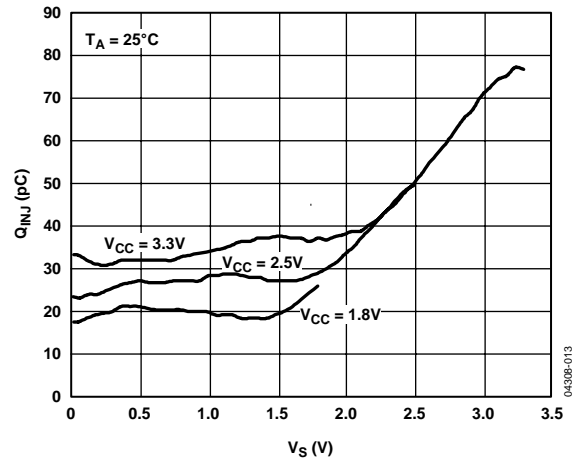


Figure 13. Charge Injection vs. Source Voltage

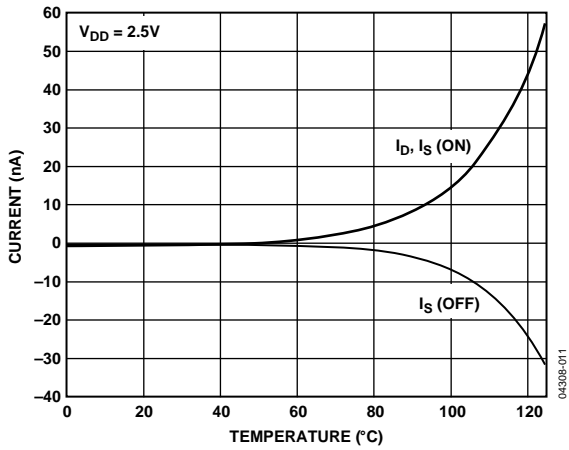


Figure 11. Leakage Current vs. Temperature, 2.5 V

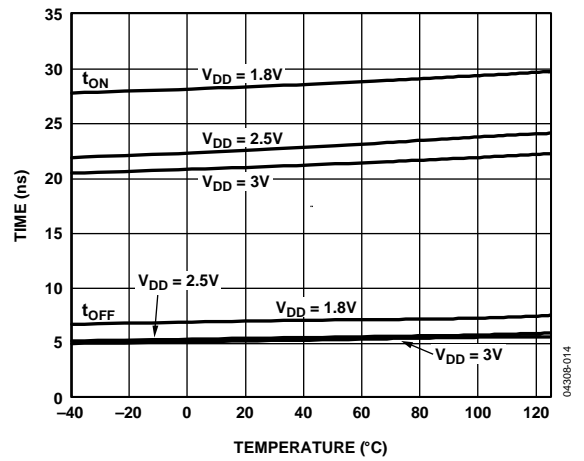


Figure 14. t_{ON}/t_{OFF} Times vs. Temperature

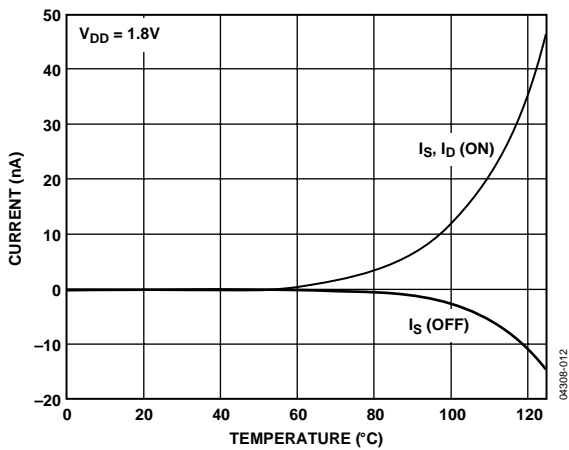


Figure 12. Leakage Current vs. Temperature, 1.8 V

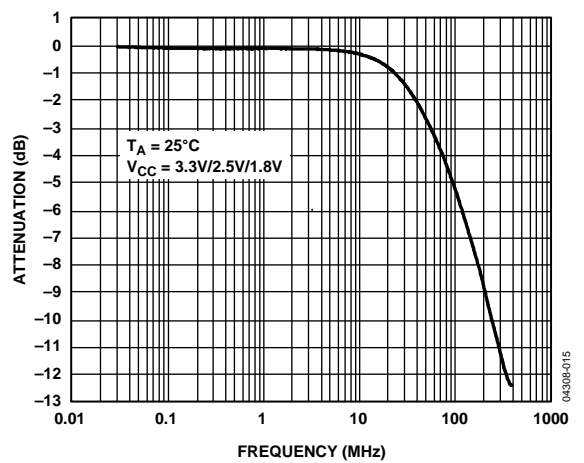


Figure 15. Bandwidth

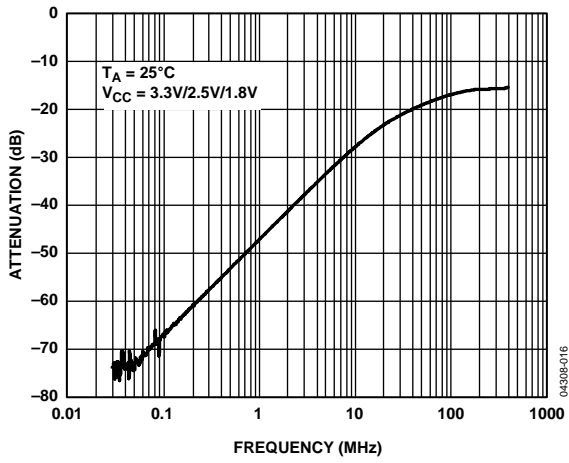


Figure 16. Off Isolation vs. Frequency

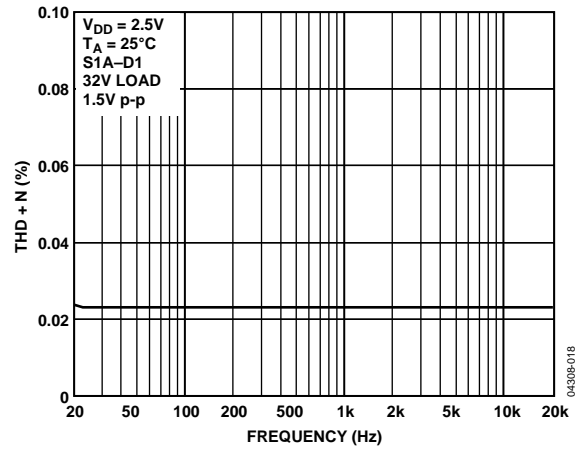


Figure 18. Total Harmonic Distortion + Noise

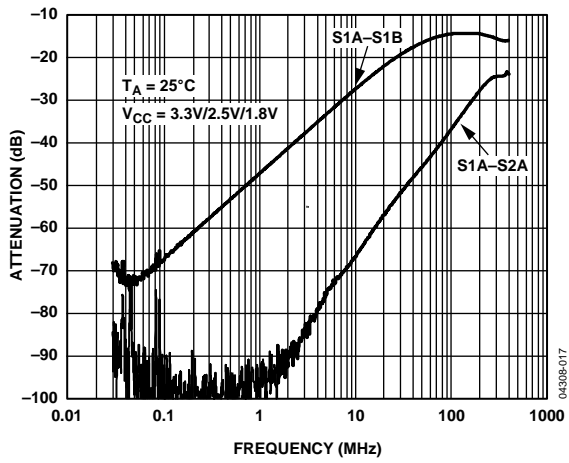
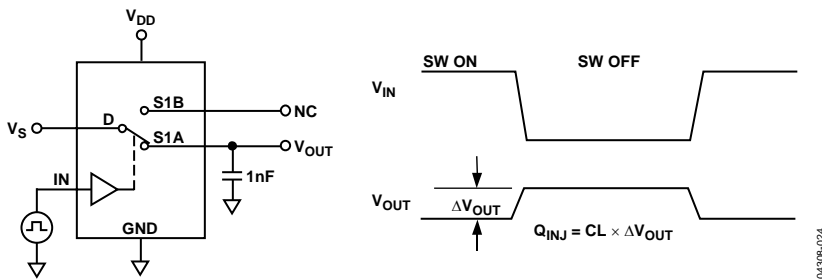
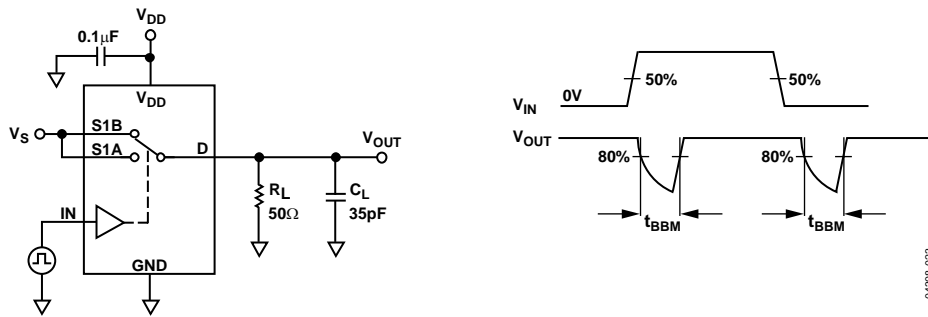
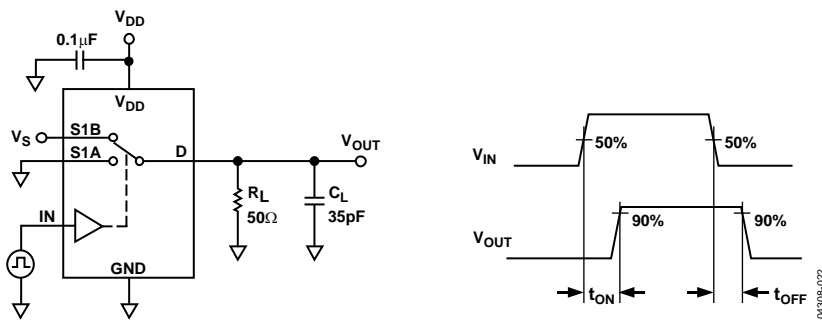
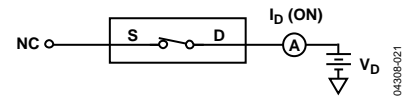
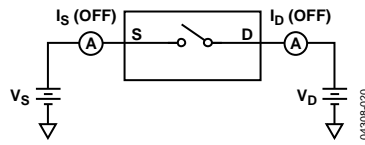
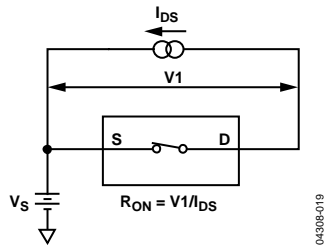


Figure 17. Crosstalk vs. Frequency

TEST CIRCUITS



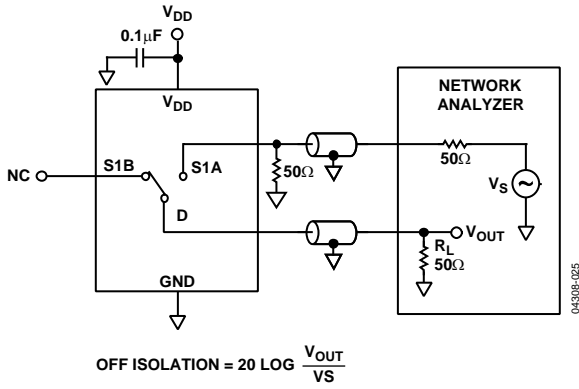


Figure 25. Off Isolation

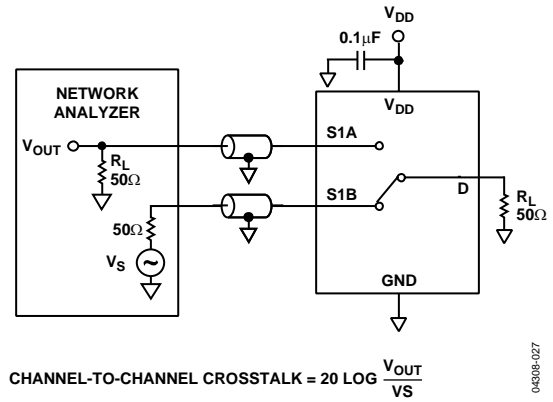


Figure 27. Channel-to-Channel Crosstalk (S1A-S1B)

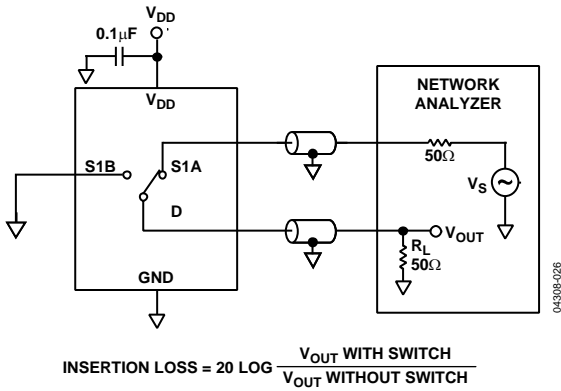


Figure 26. Bandwidth

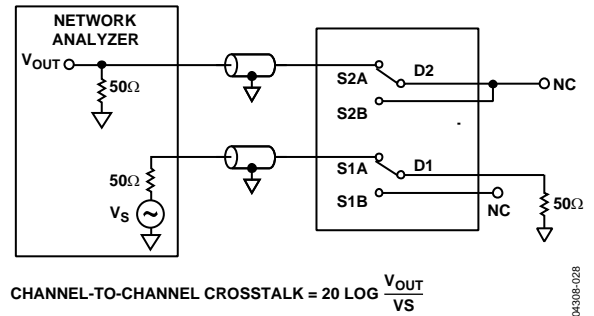
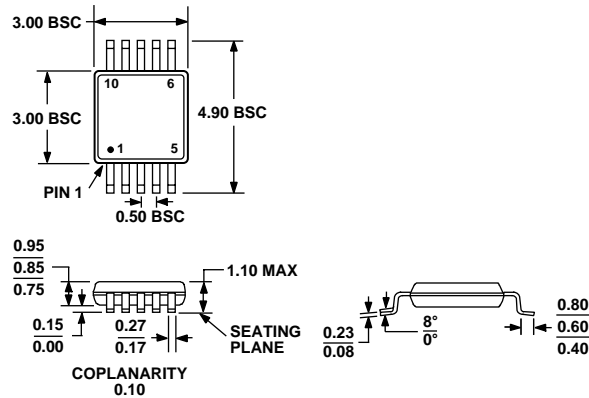


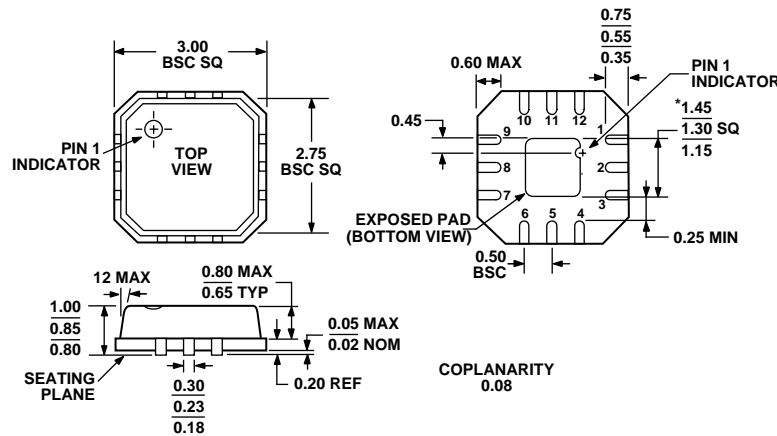
Figure 28. Channel-to-Channel Crosstalk (S1A-S2A)

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-187-BA

Figure 29. 10-Lead Mini Small Outline Package [MSOP] (RM-10)
Dimensions shown in millimeters



*COMPLIANT TO JEDEC STANDARDS MO-220-VEED-1 EXCEPT FOR EXPOSED PAD DIMENSION.

Figure 30. 12-Lead Lead Frame Chip Scale Package [LFCSP_VQ] 3 x 3 mm Body, Very Thin Quad (CP-12-1)
Dimensions shown in millimeters

ORDERING GUIDE

| Model | Temperature Range | Package Description | Package Option | Branding ¹ |
|-------------------------------|-------------------|--|----------------|-----------------------|
| ADG836YRM | -40°C to +125°C | Mini Small Outline Package (MSOP) | RM-10 | S9A |
| ADG836YRM-REEL | -40°C to +125°C | Mini Small Outline Package (MSOP) | RM-10 | S9A |
| ADG836YRM-REEL7 | -40°C to +125°C | Mini Small Outline Package (MSOP) | RM-10 | S9A |
| ADG836YRMZ ² | -40°C to +125°C | Mini Small Outline Package (MSOP) | RM-10 | S05 |
| ADG836YRMZ-REEL ² | -40°C to +125°C | Mini Small Outline Package (MSOP) | RM-10 | S05 |
| ADG836YRMZ-REEL7 ² | -40°C to +125°C | Mini Small Outline Package (MSOP) | RM-10 | S05 |
| ADG836YCP-REEL | -40°C to +125°C | Lead Frame Chip Scale Package (LFCSP_VQ) | CP-12-1 | S9A |
| ADG836YCP-REEL7 | -40°C to +125°C | Lead Frame Chip Scale Package (LFCSP_VQ) | CP-12-1 | S9A |

¹ Branding on this package is limited to three characters due to space constraints.

² Z = Pb-free part.

ADG836

NOTES

NOTES

ADG836

NOTES



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.